



# 《风光欣》技术资料

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## 2SB1132

## PNP EPITAXIAL SILICON TRANSISTOR

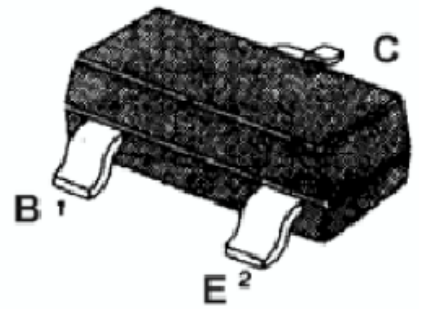
### ●Features

- 1) LOW  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = -0.2V$  (Typ.)  
 $(I_c / I_B = -500mA / -50mA)$
- 2) Compliments 2SD1664 /  
 2SD1858.

### ABSOLUTE MAXIMUM RATINGS(TA=25 )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-32	V
Emitter -Base Voltage	$V_{EB0}$	-5	V
Collector Current (DC)	$I_c$	-1	A
Base Current (DC)	$I_B$	-0.6	A
Collector Dissipation (Ta=25 )	$P_c$	300	mW
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~150	

SOT-23



### ELECTRICAL CHARACTERISTICS(TA=25 )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cut-off Current	$I_{CB0}$	$V_{CB} = -20V, I_E = 0$			-1	$\mu A$
Emitter-Cut-off Current	$I_{EB0}$	$V_{EB} = -4V, I_C = 0$			-1	$\mu A$
*DC Current Gain	$H_{fe}$	$V_{CE} = -3V, I_c = -0.1A$	82		390	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.2	-0.5	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = -5V, I_E = -50mA, f = 30MHz$		150		MHZ
Output Capacitance	$C_{OB}$	$V_{CE} = -10V, I_E = 0, f = 1MHz$		20	30	pF

### hFE (2) CLASSIFICATION

Classification	P	Q	R
HFE(2)	82-180	120-270	180-390